

HALOGEN

FREE



## 300 MHz, 2.5 $\Omega$ , Dual SPDT Analog Switches

## **DESCRIPTION**

The DG3516, DG3517 are dual SPDT analog switches which operate from 1.8 V to 5.5 V single rail power supply. They are design for audio, video, and USB switching applications.

The devices have 2.5  $\Omega$  on-resistance and 300 MHz 3dB bandwidth. 0.2  $\Omega$  on-resistance matching and 1  $\Omega$  flatness make the device high linearity. The devices are 1.6 V logic compatible within the full operation voltage range.

These switches are built on a sub-micron high density process that brings low power consumption and low voltage performance.

The switches are packaged in MICRO FOOT chip scale package of 4 mm x 3 mm bump array.

As a committed partner to the community and environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For MICRO FOOT analog switch products manufactured with tin/silver/copper (SnAgCu) device termination, the lead (Pb)-free "-E1" suffix is being used as a designator.

#### **FEATURES**

- Halogen-free according to IEC 61249-2-21 Definition
- 1.8 V to 5.5 V operation
- 2.5  $\Omega$  at 2.7 V R<sub>ON</sub>
- 300 MHz 3 dB bandwidth
- ESD method 3015.7 > 2 kV
- Latch-up current 200 mA (JESD 78)
- 1.6 V logic compatible
- Compliant to RoHS Directive 2002/95/EC

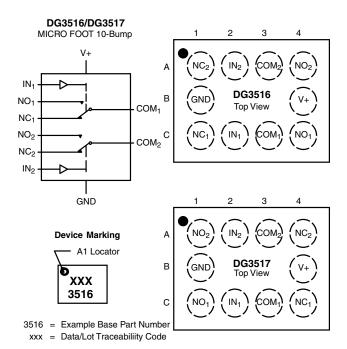
#### BENEFITS

- Space Saving MICRO FOOT® Package
- **High Linearity**
- Low Power Consumption
- High Bandwidth
- Full Rail Signal Swing Range

#### **APPLICATIONS**

- Cellular Phones
- MP3
- Media Players
- Modems
- Hard Drives
- **PCMCIA**

## **FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION**



TRUTH TABLE							
Logic	NC1 and NC2	NO1 and NO2					
0	ON	OFF					
1	OFF	ON					

ORDERING INFORMATION						
Temp. Range	Package	Part Number				
- 40 °C to 85 °C	MICRO FOOT: 10 Bump (4 x 3, 0.5 mm Pitch, 238 µm Bump Height)	DG3516DB-T5-E1 DG3517DB-T5-E1				

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ABSOLUTE MAXIMUM RATINGS						
Parameter	Limit	Unit				
Reference V+ to GND		- 0.3 to + 6	V			
IN, COM, NC, NO <sup>a</sup>	- 0.3 to (V+ + 0.3)	V				
Continuous Current (NO, NC, COM)	± 100	mA				
Peak Current (Pulsed at 1 ms, 10 % du	± 200	IIIA				
Storage Temperature	(D Suffix)	- 65 to 150	00			
Package Solder Reflow Conditions <sup>b</sup>	250	°C				
ESD per Method 3015.7	> 2	kV				
Power Dissipation (Packages) <sup>c</sup>	MICRO FOOT: 10 Bump (4 mm x 3 mm) <sup>d</sup>	457	mW			

#### Notes:

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. Refer to IPC/JEDEC (J-STD-020B).
- c. All bumps welded or soldered to PC board.
- d. Derate 5.7 mW/°C above 70 °C.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS (V+ = 3 V)									
		Test Conditions Otherwise Unless Specified			<b>Limits</b> - 40 °C to 85 °C				
Parameter	Symbol	V+ = 2.7 V  to  3.6 V	$V_{IN} = 0.5 \text{ V or } 1.4 \text{ V}^{e}$	Temp.a	Min.b	Typ. <sup>c</sup>	Max.b	Unit	
Analog Switch									
Analog Signal Range <sup>d</sup>	$V_{NO}, V_{NC}, V_{COM}$			Full	0		V+	٧	
On-Resistance <sup>d</sup>	R <sub>ON</sub>		V <sub>COM</sub> = 1.5 V	Room Full		2.5	3.5 3.8		
R <sub>ON</sub> Flatness <sup>d</sup>	R <sub>ON</sub> Flatness	V+ = 2.7 V $I_{NO}$ , $I_{NC} = 10 \text{ mA}$		V <sub>COM</sub> = 1, 1.5, 2 V	Room		0.52	1	Ω
On-Resistance Match Between Channels <sup>d</sup>	$\Delta R_{DS(on)}$		V <sub>COM</sub> = 1.5 V	Room			0.25		
Switch Off Leakage Current	I <sub>NO(off)</sub> I <sub>NC(off)</sub>	V+ = 3.3 V, V <sub>NO</sub> , V <sub>NC</sub> = 0.3 V/3 V, V <sub>COM</sub> = 3 V/0.3 V		Room Full	- 2 - 20		2 20		
Switch On Leakage Current	I <sub>COM(off)</sub>			Room Full	- 2 - 20		2 20	nA	
Channel-On Leakage Current	I <sub>COM(on)</sub>	$V+ = 3.3 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 0.3 \text{ V/3 V}$		Room Full	- 2 - 20		2 20		
Digital Control									
Input High Voltage <sup>d</sup>	$V_{INH}$			Full	1.4			V	
Input Low Voltage	V <sub>INL</sub>			Full			0.5	] "	
Input Capacitance	C <sub>in</sub>			Full		5		pF	
Input Current	I <sub>INL</sub> or I <sub>INH</sub>	$V_{IN} = 0$	) V or V+	Full	1		1	μΑ	



SPECIFICATIONS (V+ = 3 V)									
		Test Conditions Otherwise Unless Specified			- 40	Limits O °C to 85	s °C		
Parameter	Symbol	V+ = 2.7 V to 3.6 V, V	$I_{IN} = 0.5 \text{ V or } 1.4 \text{ V}^{e}$	Temp.a	Min. <sup>b</sup>	Typ. <sup>c</sup>	Max.b	Unit	
Dynamic Characteristics									
Turn-On Time	t <sub>ON</sub>	V+ = 2.7 V, $V_{NO}$ or $V_{NC}$ = 1.5 V $R_L$ = 300 Ω, $C_L$ = 35 pF		Room Full		21	51 52		
Turn-Off Time	t <sub>OFF</sub>			Room Full		15	45 46	ns	
Break-Before-Make Time	t <sub>d</sub>			Full	1				
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L = 1 \text{ nF, } V_{GEN} = 2 \text{ V, } R_{GEN} = 0 \Omega$		Room		1		рС	
Off-Isolation <sup>d</sup>	OIRR	f = 1 MHz	Room		- 74				
Off-Isolation <sup>2</sup>	Oinn	$R_L = 50 \Omega$ , $C_L = 5 pF$	f = 10 MHz	Room		- 54		dB	
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	11L = 30 32, OL = 3 pi	f = 1 MHz	Room		- 76		ub	
Crossiaik	MALK		f = 10 MHz	Room		- 56			
N. N. Off Canacitanas <sup>d</sup>	C <sub>NO(off)</sub>			Room		12			
N <sub>O</sub> , N <sub>C</sub> Off Capacitance <sup>d</sup>	C <sub>NC(off)</sub>	$V_{IN} = 0$ or $V+$ , $f = 1$ MHz		Room		12		pF	
01	C <sub>NO(on)</sub>	V <sub>IN</sub> = 0 01 V+, 1 = 1 MITIZ		Room		40		- pr	
Channel-On Capacitance <sup>d</sup>	C <sub>NC(on)</sub>			Room		40			
Power Supply									
Power Supply Current	I+	V <sub>IN</sub> = 0 V	or V+	Room Full			1 1	μΑ	



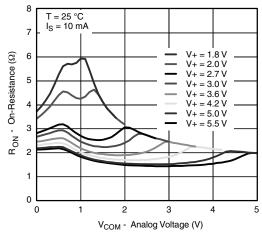
SPECIFICATIONS (V+	= 5 V)							
		Test Conditions Otherwise Unless Specified			- 40	Limits - 40 °C to 85 °C		
Parameter	Symbol	$V+$ = 4.2 V to 5.5 V, $V_{IN}$ = 0.8 V or 2 $V^e$		Temp.a	Min.b	Typ.c	Max.b	Unit
Analog Switch								
Analog Signal Range <sup>d</sup>	V <sub>NO</sub> , V <sub>NC</sub> , V <sub>COM</sub>			Full	0		V+	V
On-Resistance <sup>d</sup>	R <sub>ON</sub>		V <sub>COM</sub> = 3.5 V	Room Full		2.2	2.9 3.1	
R <sub>ON</sub> Flatness <sup>d</sup>	R <sub>ON</sub> Flatness	V+ = 4.2 V $I_{NO}$ , $I_{NC} = 10 \text{ mA}$	V <sub>COM</sub> = 1, 2, 3.5 V	Room		0.53	1	Ω
On-Resistance Match Between Channels <sup>d</sup>	$\Delta R_{DS(on)}$		V <sub>COM</sub> = 3.5 V	Room			0.25	
Switch Off Leakage Current	I <sub>NO(off)</sub> I <sub>NC(off)</sub>		5.5 V,	Room Full	- 2 - 20		2 20	
Switch On Leakage Current	I <sub>COM(off)</sub>	$V_{NO}, V_{NC} = 1 \text{ V}/4.5$	$V, V_{COM} = 4.5 V/1 V$	Room Full	- 2 - 20		2 20	nA
Channel-On Leakage Current	I <sub>COM(on)</sub>	$V+ = 5.5 V, V_{NO}, V_{NO}$	$_{IC} = V_{COM} = 1 \text{ V/4.5 V}$	Room Full	- 2 - 20		2 20	
Digital Control								
Input High Voltage <sup>d</sup>	$V_{INH}$			Full	2			V
Input Low Voltage	V <sub>INL</sub>			Full			0.8	<b>'</b>
Input Capacitance	C <sub>in</sub>					5		pF
Input Current	I <sub>INL</sub> or I <sub>INH</sub>	V <sub>IN</sub> = 0 or V+		Full	1		1	μΑ
Dynamic Characteristics								
Turn-On Time	t <sub>ON</sub>	V+ - 42 V V	NO or V <sub>NC</sub> = 3 V	Room Full		15	45 46	
Turn-Off Time	t <sub>OFF</sub>	-	$C_{L} = 35 \text{ pF}$	Room Full		12	42 43	ns
Break-Before-Make Time	t <sub>d</sub>			Full	1			
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L = 1 \text{ nF, } V_{GEN}$	= 2 V, $R_{GEN} = 0 \Omega$	Room		1		рC
Off-Isolation <sup>d</sup>	OIRR		f = 1 MHz	Room		- 74		
On-isolation	0	$R_L = 50 \Omega$ , $C_L = 5 pF$	f = 10 MHz	Room		- 54		dB
Crosstalk <sup>d</sup>			f = 1 MHz	Room		- 78		
		f = 10 MHz		Room		- 56		
N <sub>O</sub> , N <sub>C</sub> Off Capacitance <sup>d</sup>	C <sub>NO(off)</sub>	V <sub>IN</sub> = 0 or V+, f = 1 MHz		Room		12		pF
	C <sub>NC(off)</sub>			Room		12		
Channel-On Capacitance <sup>d</sup>	$C_{NO(on)}$			Room		40		4
Power Supply	ONC(on)			Hoom		40		
				Room			1	
Power Supply Current	I+	$V_{IN} = 0 V \text{ or } V+$		Full			1	μΑ

## Notes:

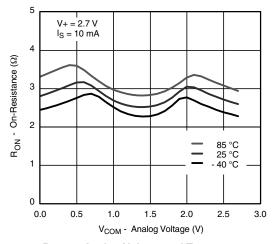
- a. Room =  $25 \, ^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- d. Guarantee by design, nor subjected to production test.
- e.  $V_{IN}$  = input voltage to perform proper function.
- f. Guaranteed by 5 V testing, not production tested.



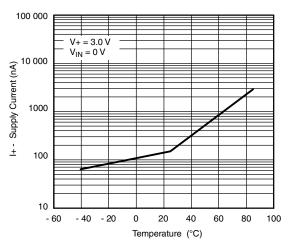
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



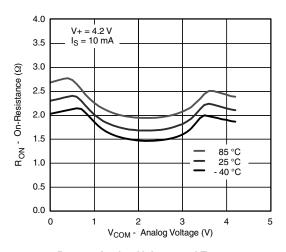
 $R_{ON}$  vs.  $V_{COM}$  and Single Supply Voltage



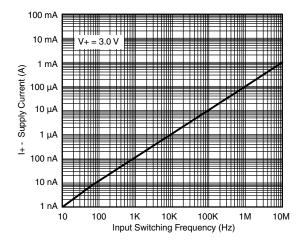
R<sub>ON</sub> vs. Analog Voltage and Temperature



Supply Current vs. Temperature

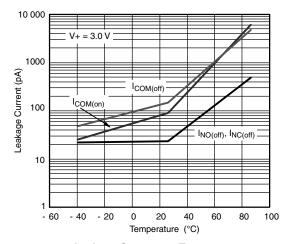


R<sub>ON</sub> vs. Analog Voltage and Temperature

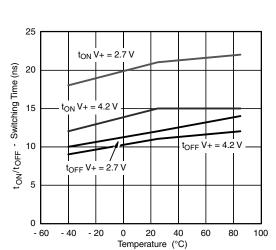


**Supply Current vs. Input Switching Frequency** 

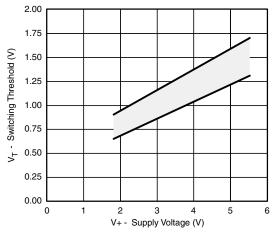
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



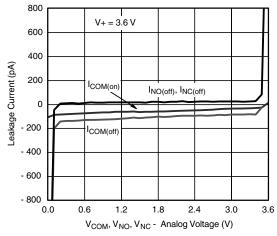
Leakage Current vs. Temperature



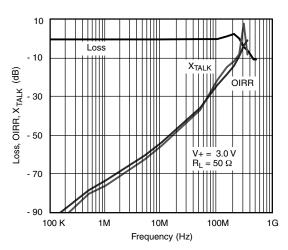
Switching Time vs. Temperature



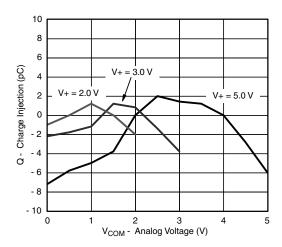
Switching Threshold vs. Supply Voltage



Leakage vs. Analog Voltage



Insertion Loss, Off-Isolation Crosstalk vs. Frequency

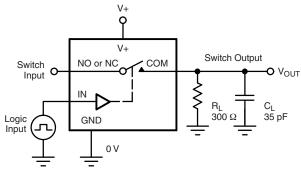


Charge Injection vs. Analog Voltage



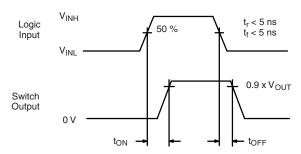


## **TEST CIRCUITS**



C<sub>L</sub> (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left( \frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

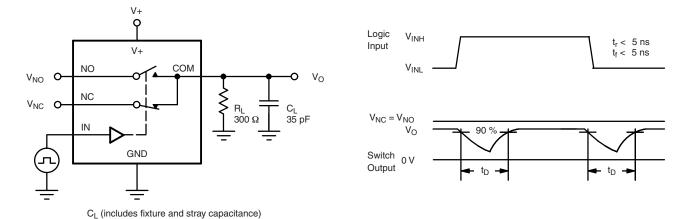


Figure 2. Break-Before-Make Interval

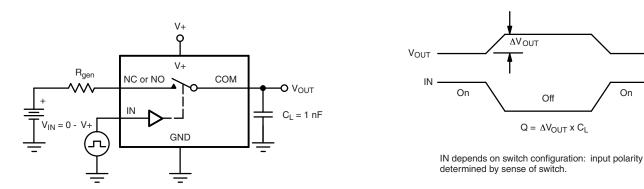


Figure 3. Charge Injection

On

## **TEST CIRCUITS**



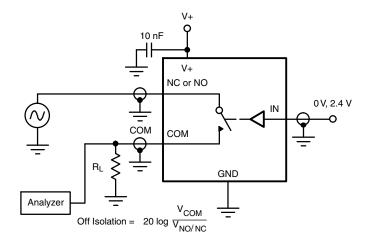


Figure 4. Off-Isolation

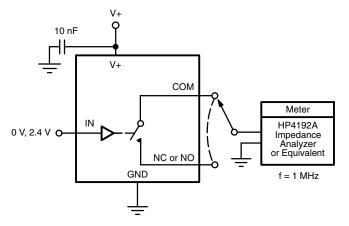
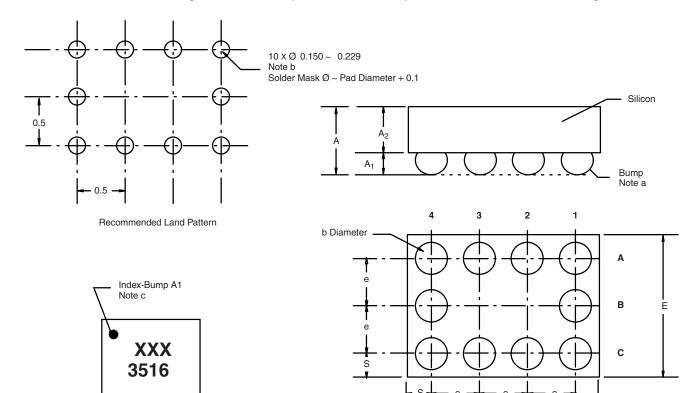


Figure 5. Channel Off/On Capacitance



### **PACKAGE OUTLINE**

## MICRO FOOT: 10 BUMP (4 mm x 3 mm, 0.5 mm PITCH, 0.238 mm BUMP HEIGHT)



Notes (Unless Otherwise Specified):

- a. Bump is Lead (Pb)-free Sn/Ag/Cu.
- b. Non-solder mask defined copper landing pad.

Top Side (Die Back)

c. Laser Mark on silicon die back; back-lapped, no coating. Shown is not actual marking; sample only.

Dim.	Millin	neters <sup>a</sup>	Inches			
Dilli.	Min.	Max.	Min.	Max.		
Α	0.688	0.753	0.0271	0.0296		
A <sub>1</sub>	0.218	0.258	0.0086	0.0102		
A <sub>2</sub>	0.470	0.495	0.0185	0.0195		
b	0.306	0.346	0.0120	0.0136		
D	1.980	2.020	0.0780	0.0795		
E	1.480	1.520	0.0583	0.0598		
е	0.5 E	5 BASIC 0.0197 BASIC		BASIC		
S	0.230	0.270	0.0091	0.0106		

#### Notes:

a. Use millimeters as the primary measurement.

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